



LIS2L02AS

INERTIAL SENSOR: 2Axis - 2g/6g LINEAR ACCELEROMETER

PRODUCT PREVIEW

- 3V TO 5.25V SINGLE SUPPLY OPERATION
- THE SENSITIVITY IS ADJUSTED WITH A TOTAL ACCURACY OF $\pm 10\%$
- THE OUTPUT VOLTAGE, OFFSET, SENSITIVITY AND TEST VOLTAGE ARE RATIO-METRIC TO THE SUPPLY VOLTAGE
- DEVICE SENSITIVITY IS ON-CHIP FACTORY TRIMMED
- EMBEDDED SELF TEST
- HIGH SHOCK SURVIVABILITY

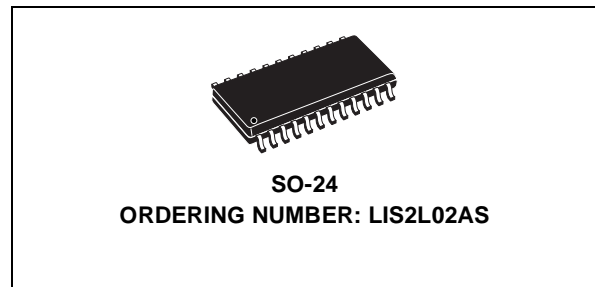
DESCRIPTION

The LIS2L02AS is a dual-axis linear accelerometer that includes a sensing element and an IC interface able to take the information from the sensing element and to provide an analog signal to the external world.

The sensing element, capable to detect the acceleration, is manufactured using a dedicated process called THELMA (Thick Epi-Poly Layer for Microactuators and Accelerometers) developed by ST to produce inertial sensors and actuators in silicon.

The IC interface instead is manufactured using a CMOS process that allows high level of integration to design a dedicated circuit which is trimmed to better match the sensing element characteristics.

The LIS2L02AS has a user selectable full scale of 2g, 6g and it is capable of measuring accelerations over



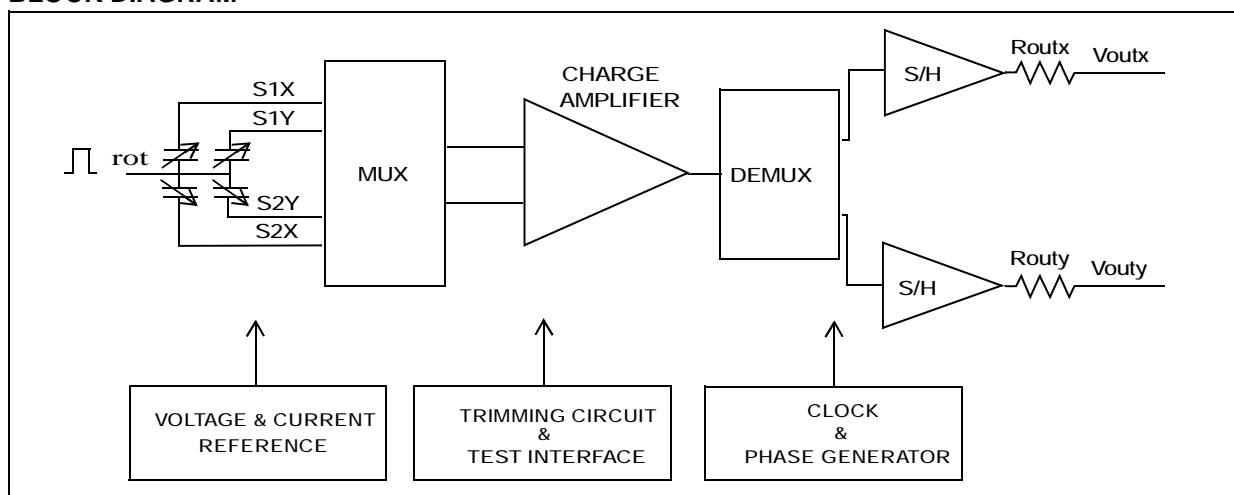
a maximum bandwidth of 4.0 KHz for both the X and Y axis. The device bandwidth may be reduced by using external capacitances. A self-test capability allows the user to check the functioning of the system.

The LIS2L02AS is available in plastic SMD package and it is specified over a temperature range extending from -40°C to $+85^{\circ}\text{C}$.

The LIS2L02AS belongs to a family of products suitable for a variety of applications:

- Antitheft systems
- Inertial navigation
- Virtual reality input devices
- Vibration Monitoring, recording and compensation
- Appliance control
- Robotics

BLOCK DIAGRAM

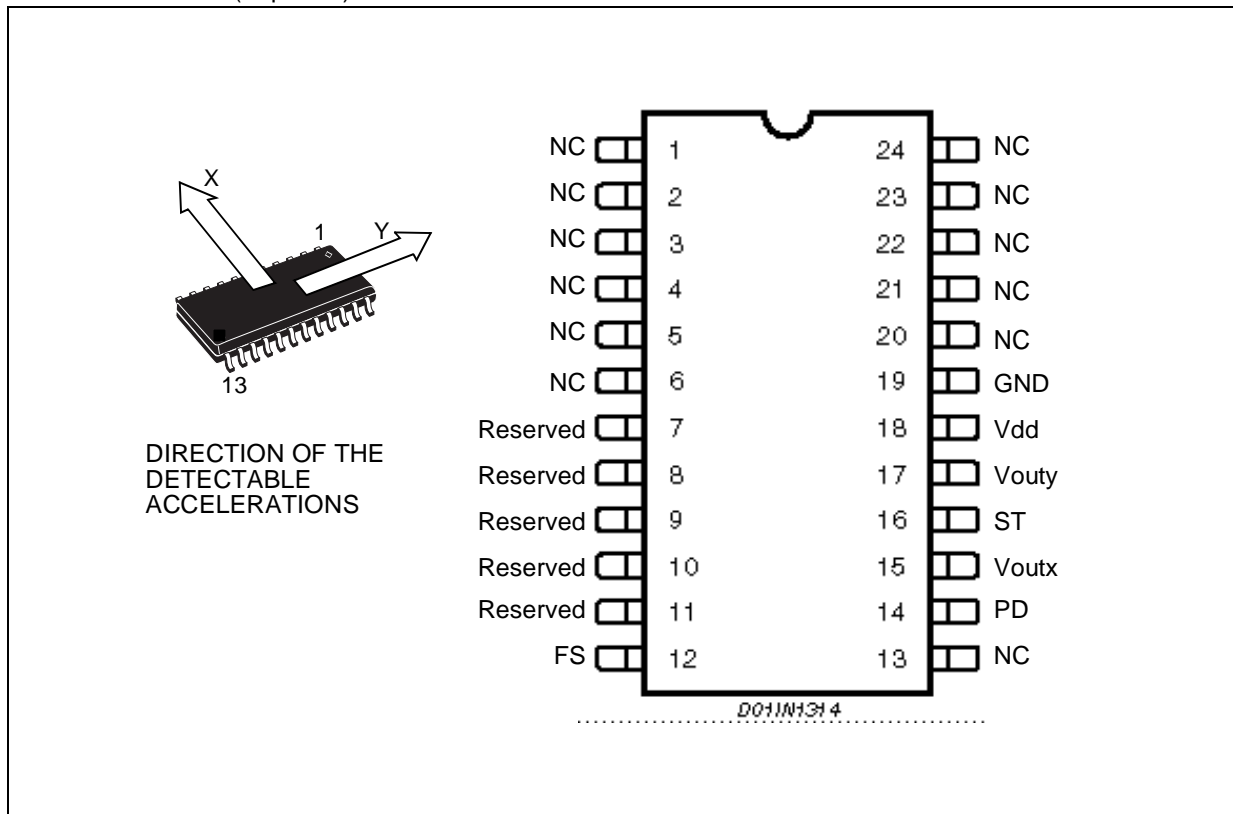


LIS2L02AS

PIN DESCRIPTION

N°	Pin	Function
1 to 6	NC	Internally not connected
7	Reserved	Leave unconnected or connect to ground
8	Reserved	Leave unconnected or connect to Vdd
9	Reserved	Connect to Vdd or ground
10-11	Reserved	Leave unconnected or connect to Vdd
12	FS	Full Scale selection (Logic 0: 2g Full-scale; Logic 1: 6g Full-scale)
13	NC	Internally not connected
14	PD	Power Down (Logic 0: normal mode; Logic 1: Power-Down mode)
15	Voutx	Output Voltage
16	ST	Self Test (Logic 0: normal mode; Logic 1: Self-test)
17	Vouty	Output Voltage
18	Vdd	Power supply
19	GND	0V supply
20 to 24	NC	Internally not connected

PIN CONNECTION (Top view)



ELECTRICAL CHARACTERISTICS (Temperature range -40°C to +85°C)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V _{dd}	Supply voltage		3		5.25	V
I _{dd}	Supply current			1.0		mA
V _{off}	Zero-g level	T _{amb} = 25°C ratiometric to V _{dd}	V _{dd} /2-10%	V _{dd} /2	V _{dd} /2+10%	V
A _r	Acceleration range	0V on FS pin	±1.8	±2.0	±2.2	g
		V _{dd} on FS pin		±±6.0		g
S _o	Sensitivity ratiometric to V _{dd}	T _{amb} = 25°C Full-scale = 2g	V _{dd} /5-10%	V _{dd} /5	V _{dd} /5+10%	V/g
		T _{amb} = 25°C Full-scale = 6g	V _{dd} /15-10%	V _{dd} /15	V _{dd} /15+10%	V/g
N _L	Non Linearity	Best fit straight line X, Y axis Full-scale = 2g		±0.3		%
f _{uc}	Sensing Element Resonant Frequency	X, Y axis		4.0		KHz
a _n	Acceleration noise density	V _{dd} = 5V Full-scale = 2g		50		μg/√Hz
V _t	Self test output voltage Ratiometric to V _{dd}	T _{amb} = 25°C @ 5V	100			mV
V _{st}	Self test input	Logic 0 level	0		0.8	V
		Logic 1 level	2.8		V _{dd}	V
R _{out}	Output impedance			100		kΩ
C _{load}	Capacitive load drive		320			pF

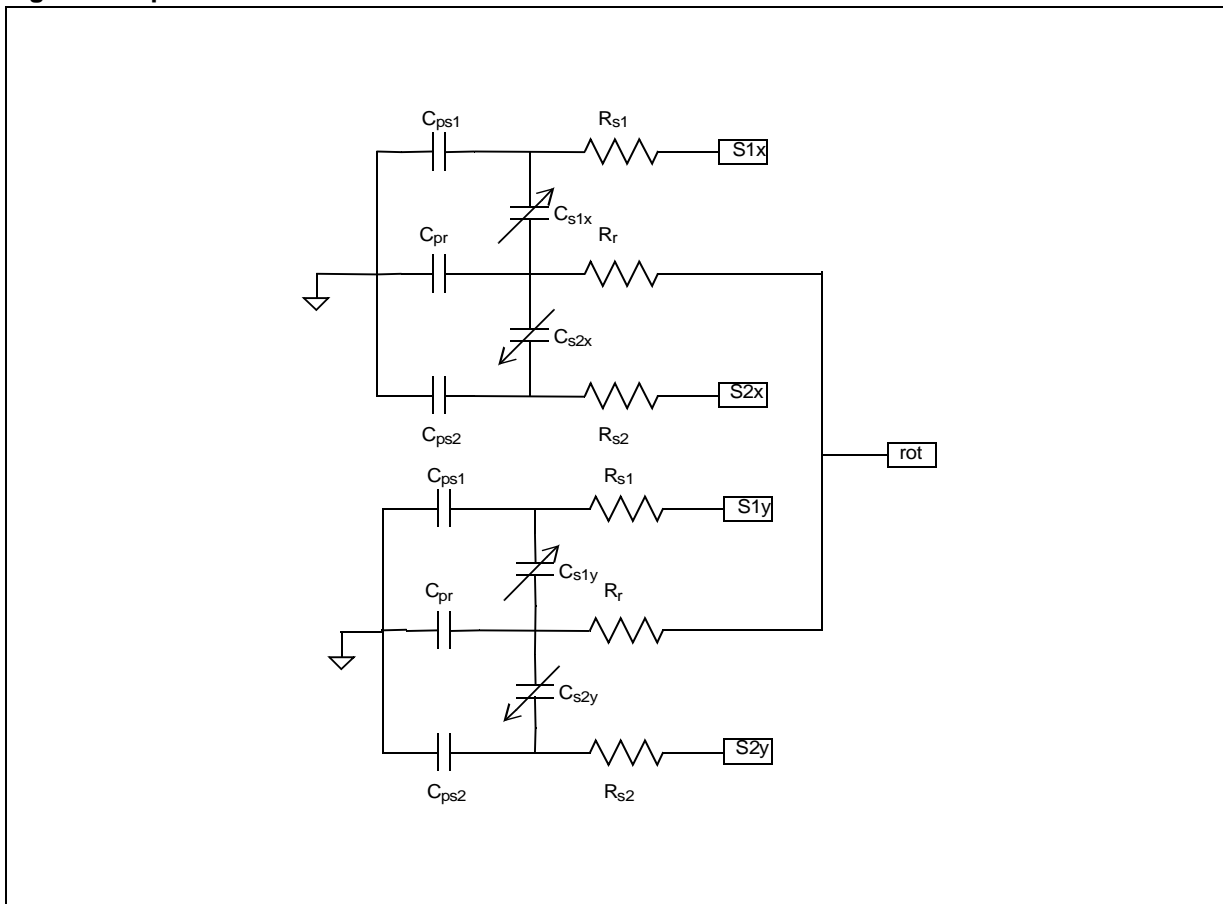
1 FUNCTIONALITY**1.1 Sensing element**

The THELMA process is utilized to create a surface micro-machined accelerometer. The technology allows to carry out suspended silicon structures which are attached to the substrate in a few points called anchors and free to move on a plane parallel to the substrate itself. To be compatible with the traditional packaging techniques a cap is placed on top of the sensing element to avoid blocking the moving parts during the molding phase.

The equivalent circuit for the sensing element is shown in the below figure; when a linear acceleration is applied, the proof mass displaces from its nominal position, causing an imbalance in the capacitive half-bridge. This imbalance is measured using charge integration in response to a voltage pulse applied to the sense capacitor.

The nominal value of the capacitors, at steady state, is few pF and when an acceleration is applied the maximum variation of the capacitive load is few tenth of pF.

Figure 1. Equivalent electrical circuit



1.2 IC Interface

The complete signal processing uses a fully differential structure, while the final stage converts the differential signal into a single-ended one to be compatible with the external world.

The first stage is a low-noise capacitive amplifier that implements a Correlated Double Sampling (CDS) at its output to cancel the offset and the $1/f$ noise. The produced signal is then sent to two different S&Hs, one for each channel, and made available to the outside.

The low noise input amplifier operates at 200 kHz while the two S&Hs operate at a sampling frequency of 66 kHz. This allows a large oversampling ratio, which leads to in-band noise reduction and to an accurate output waveform.

All the analog parameters (output offset voltage and sensitivity) are ratiometric to the voltage supply. Increasing or decreasing the voltage supply, the sensitivity and the offset will increase or decrease linearly. The feature provides the cancellation of the error related to the voltage supply along an analog to digital conversion chain.

1.3 Factory calibration

The IC interface is factory calibrated to provide to the final user a device ready to operate. The parameters which are trimmed are: gain, offset, common mode and internal clock frequency.

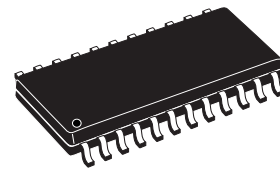
The trimming values are stored inside the device by a poly-fuse structure. Any time the device is turned on, the memorized bits are downloaded into the registers to be employed during the normal operation. The poly-fuse approach allows the final user to utilize the device without any need for further calibration

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.35		2.65	0.093		0.104
A1	0.10		0.30	0.004		0.012
B	0.33		0.51	0.013		0.200
C	0.23		0.32	0.009		0.013
D (1)	15.20		15.60	0.598		0.614
E	7.40		7.60	0.291		0.299
e		1.27			0.050	
H	10.0		10.65	0.394		0.419
h	0.25		0.75	0.010		0.030
L	0.40		1.27	0.016		0.050
k	0° (min.), 8° (max.)					
ddd			0.10			0.004

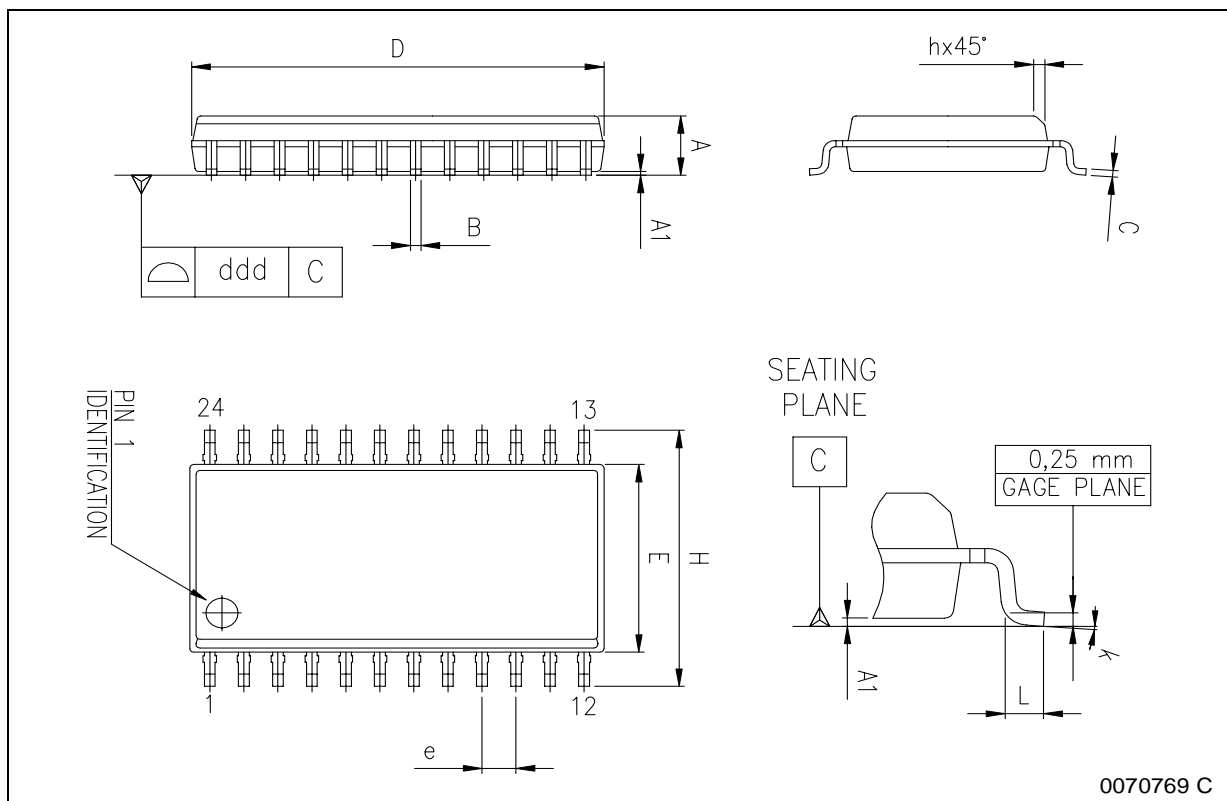
(1) "D" dimension does not include mold flash, protusions or gate burrs. Mold flash, protusions or gate burrs shall not exceed 0.15mm per side.

OUTLINE AND MECHANICAL DATA

Weight: 0.60gr



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